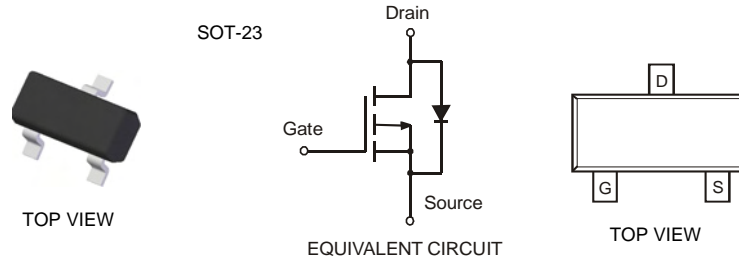


## Features

- Low On-Resistance:  
100mΩ @  $V_{GS} = -10V, I_D = -2.7A$   
170mΩ @  $V_{GS} = -4.5V, I_D = -2.0A$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 4)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



## Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Drain Current (Note 1)	Steady State	$T_A = 25^\circ C$	$I_D$	-2.7	A
		$T_A = 70^\circ C$		-2	
Pulsed Drain Current (Note 3)			$I_{DM}$	8	A

## Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_D$	1.08	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$ (Note 1)	$R_{\theta JA}$	115	$^\circ C/W$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ C$

## Electrical Characteristics @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-800	nA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 80$ $\pm 800$	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 15V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-1.3	-1.8	-2.1	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	97	100	mΩ	$V_{GS} = -10V, I_D = -2.7A$
		—	165	170		$V_{GS} = -4.5V, I_D = -2.0A$
Forward Transfer Admittance	$ Y_{fs} $	—	3.6	—	S	$V_{DS} = -5V, I_D = -2.7A$
Diode Forward Voltage (Note 5)	$V_{SD}$	—	—	-1.26	V	$V_{GS} = 0V, I_S = -2.7A$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	227	—	pF	$V_{DS} = -10V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	64	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	36	—	pF	

- Notes:
1. Device mounted on FR-4 PCB.  $t \leq 5$  sec.
  2. No purposefully added lead.
  3. Pulse width  $\leq 10\mu s$ , Duty Cycle  $\leq 1\%$ .
  4. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  5. Short duration pulse test used to minimize self-heating effect.

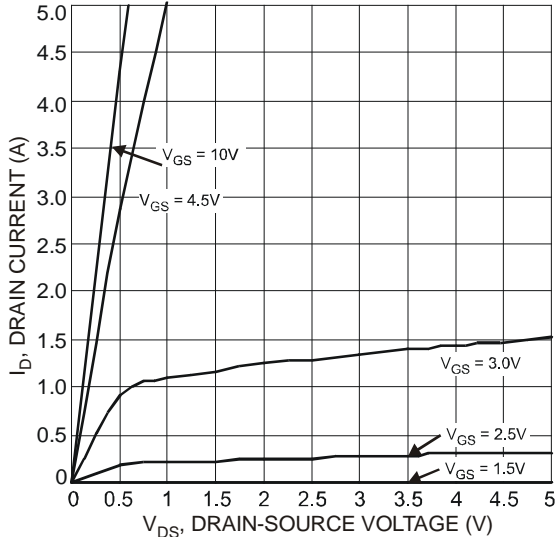


Fig. 1 Typical Output Characteristics

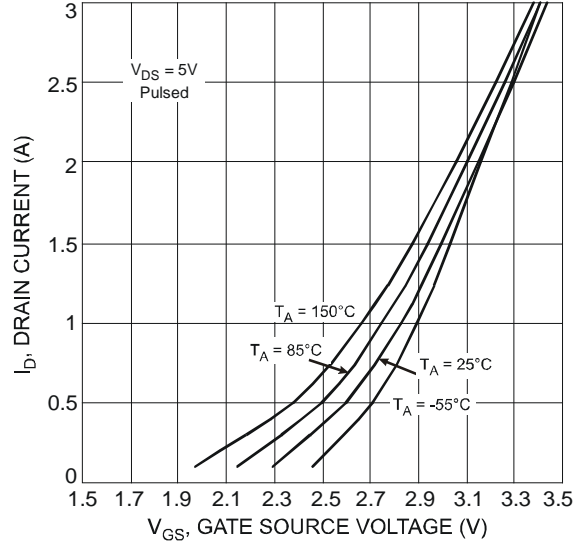


Fig. 2 Typical Transfer Characteristics

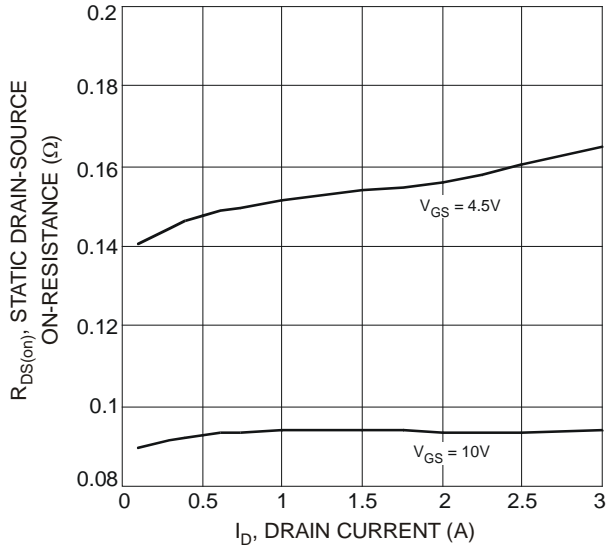


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

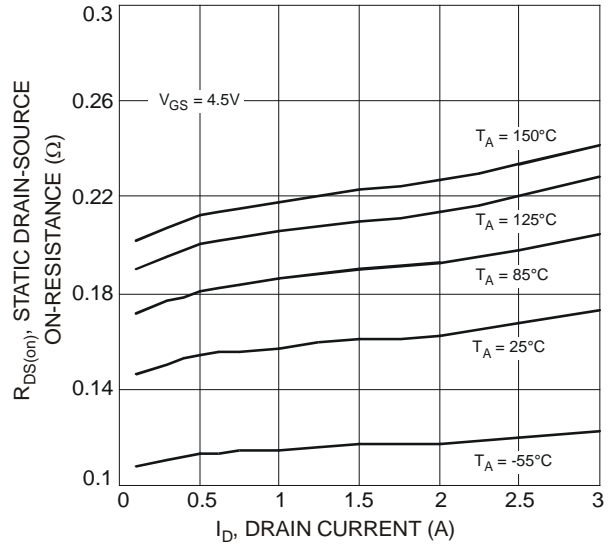


Fig. 4 On-Resistance vs. Drain Current and Gate Voltage

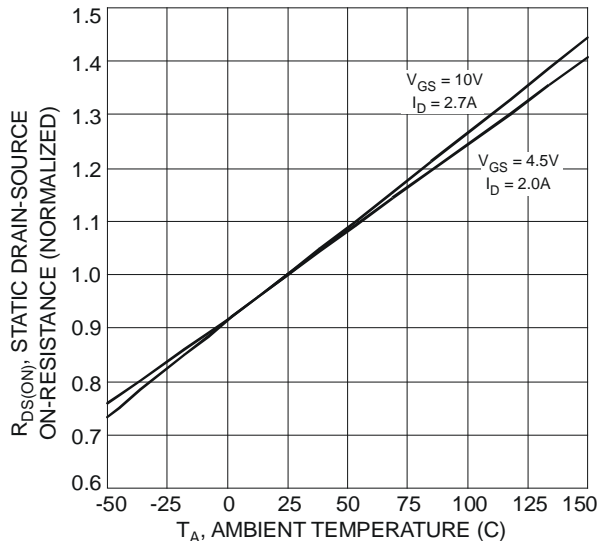


Fig. 5 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

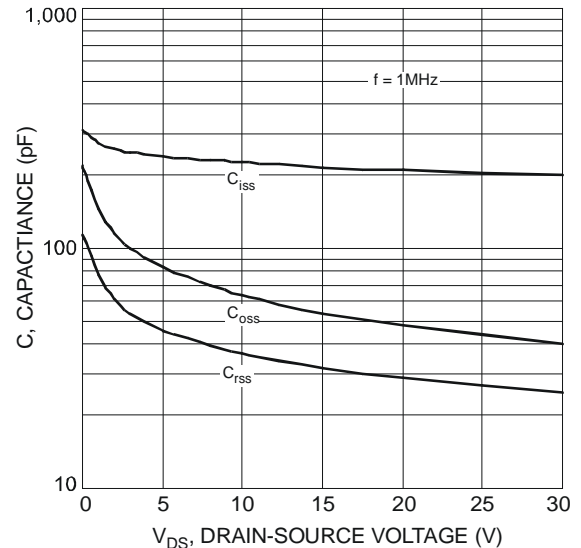


Fig. 6 Typical Capacitance

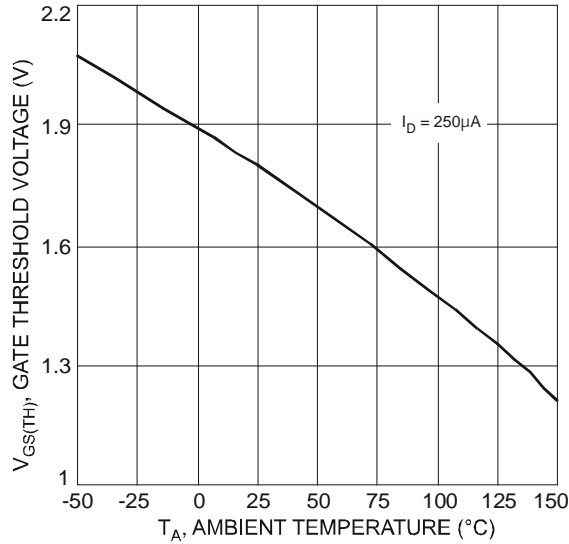


Fig. 7 Gate Threshold Voltage vs. Ambient Temperature

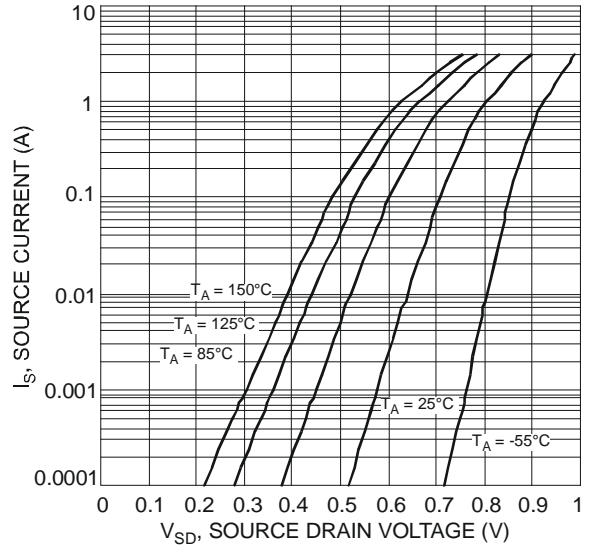


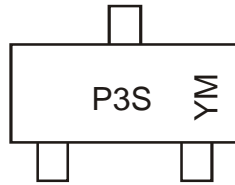
Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

**Ordering Information** (Note 6)

Part Number	Case	Packaging
DMP3100L-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



P3S = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: U = 2007  
 M = Month ex: 9 = September

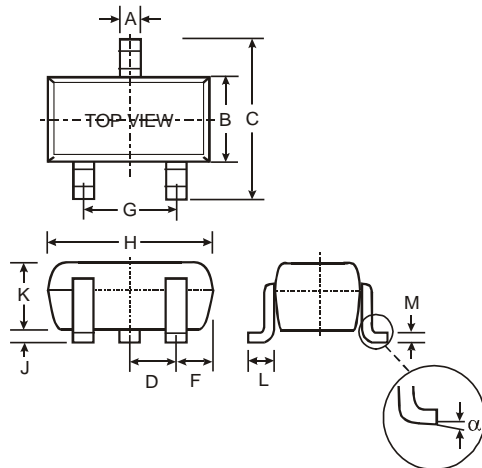
Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

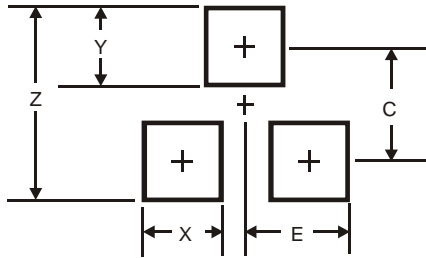
**Package Outline Dimensions**



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°

All Dimensions in mm

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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